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## Abstract

Method for fabricating a barrier layer having the following steps, namely  
oxidation of a substrate (1) composed of silicon in order to produce a substrate oxide (2) on the surface of the substrate (1);

production of an oxygen-impervious layer (4) at the interface between the substrate oxide layer (2) and the substrate (1), the oxygen-impervious layer (4), as barrier, preventing the formation of metal silicide compounds between applied metal and the substrate silicon;

etching of the substrate oxide layer (2) until the underlying oxygen-impervious layer (4) is uncovered.

Figure 3b

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## List of Reference Symbols

- 1 Substrate
- 2 Substrate oxide
- 3 Interface
- 4 Diffusion barrier layer
- 5 Ion implantation distribution
- 6 Metal layer
- 7 Metal oxide layer
- 8 Interface

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